

Silicon PNP Power Transistors

2SB857 2SB858

DESCRIPTION

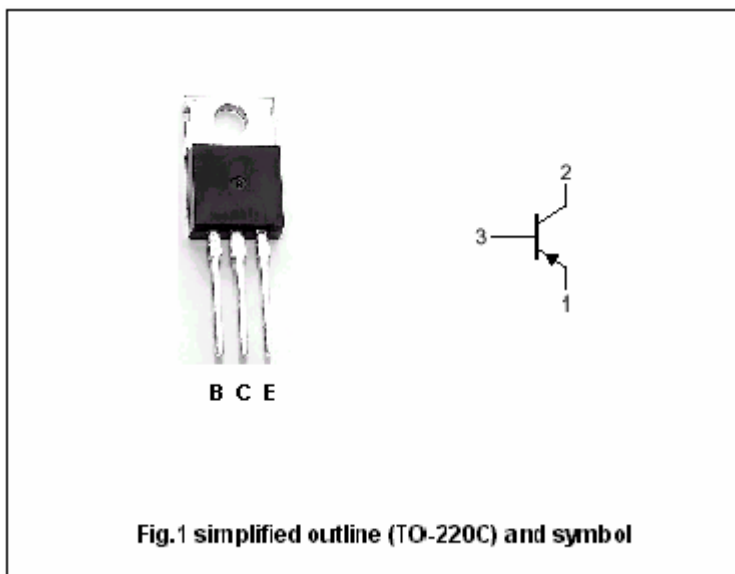
- With TO-220C package
- Complement to type 2SD1133/1134

APPLICATIONS

- Low frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	-70	V
V <sub>CEO</sub>	Collector-emitter voltage	2SB857	-50	V
		2SB858	-60	
V <sub>EBO</sub>	Emitter-base voltage	Open collector	-5	V
I <sub>C</sub>	Collector current		-4	A
I <sub>CP</sub>	Collector current-peak		-8	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	40	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-45~150	°C

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## CHARACTERISTICS

T<sub>j</sub>=25 °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	2SB857	-50			V
		2SB858	-60			
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-50mA; R <sub>BE</sub> =∞				V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>C</sub> =-10μA; I <sub>E</sub> =0	-70			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>E</sub> =-10μA; I <sub>C</sub> =0	-5			V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =-2 A; I <sub>B</sub> =-0.2 A			-1.0	V
V <sub>BE</sub>	Base-emitter voltage	I <sub>C</sub> =-1 A; V <sub>CE</sub> =-4V			-1.0	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-50V; I <sub>E</sub> =0			-1	μA
h <sub>FE-1</sub>	DC current gain	V <sub>CB</sub> =-50V; I <sub>E</sub> =0	60		320	
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-1A; V <sub>CE</sub> =-4V	35			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-4V		15		MHz

◆ h<sub>FE-1</sub> classifications

B	C	D
60-120	100-200	160-320



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